

3600.3245
August 8, 2001 (11:14AM)



Docket: AM-3245

CERTIFICATE OF MAILING

I hereby certify that this correspondence is, on the date below, being deposited with the U.S. Postal Service as first-class mail in an envelope addressed to the Commissioner of Patents and Trademarks, Washington, DC 20231.

Date: 9 August 2001

Ingrid C. Mallory
Ingrid C. Mallory

10/98
8-14-01
AIE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hoiman HUNG et al.

Attorneys Docket: AM-3245

Serial No.: 09/276,376

Art Unit No.: 1746

Filed: March 25, 1999

Examiner: A. Olsen

For: "ENHANCEMENT OF SILICON OXIDE ETCH RATE AND SUBSTRATE SELECTIVITY WITH XENON ADDITION"

Commissioner of Patents and Trademarks
Washington, DC 20231

AMENDMENT UNDER 37 CFR §1.116

Sir:

In response to the Office Action of June 14, 2000, please amend the above application as follows:

In the specification:

Paragraph at page 11, line 22 to page 12, line 4:

Two series of experiments were performed which measured oxide and nitride etch rates for blanket structures, that is, unpatterned oxide and nitride layers. The experiments used a combination of C_4F_6 and either Ar and Xe. The selectivity to nitride is plotted in FIG. 8 for the two diluent gases as a function of the diluent flows. The two diluents exhibit significantly

08/14/2001 RHONDAF1 00000103 09276376

02 FC:102

80.00 DP

RECEIVED
AUG 14 2001
TC 1700